

FORM PTO - 1449	ATTORNEY DOCKET NO.: ASC-012DV
INFORMATION DISCLOSURE STATEMENT	APPLICANTS: Lee et al.
	SERIAL NO.: Not yet assigned 10/788741
	FILING DATE: Herewith 2-27-04 GROUP: Not yet assigned

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A22	6,096,590	08/01/2000	Chan et al.			
TN	A23	6,107,653	08/22/2000	Fitzgerald			
TN	A24	6,111,267	08/29/2000	Fischer et al.			
TN	A25	6,117,750	09/12/2000	Bensahel et al.			
TN	A26	6,130,453	10/10/2000	Mei et al.			
TN	A27	6,143,636	11/07/2000	Forbes et al.			
TN	A28	6,204,529	03/20/2001	Lung et al.			
TN	A29	6,207,977 B1	03/27/2001	Augusto			
TN	A30	US 2001/0003364 A1	06/14/2001	Sugawara et al.			
TN	A31	6,249,022	06/19/2001	Lin et al.			
TN	A32	6,251,755 B1	06/26/2001	Furukawa et al.			
TN	A33	6,266,278	07/24/2001	Harari et al.			
TN	A34	US 2002/0100942 A1	08/01/2001	Fitzgerald et al. 2602			
TN	A35	6,339,232 B1	01/15/2002	Takagi			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
TN	B17	WO 02/15244A2	02/21/2002	PCT				No	Yes
TN	B18	WO 02/13262 A2	02/14/2002	PCT				No	Yes
TN	B19	WO 02/47168 A2	06/13/2002	PCT				No	Yes
TN	B20	WO 02/071488 A1	09/12/2002	PCT				No	Yes
TN	B21	WO 02/071491 A1	09/12/2002	PCT				No	Yes

## OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
TN	C18	König et al., "Design Rules for n-Type SiGe Hetero FETs," Solid State Electronics, Vol. 41, No. 10 (1997), pp. 1541-1547.
TN	C19	Höck et al., "Carrier mobilities in modulation doped Si <sub>1-x</sub> Ge <sub>x</sub> heterostructures with respect to FET applications," Thin Solid Films, Vol. 336 (1998) pp. 141-144.
EXAMINER	T. NAWJEN	
	DATE CONSIDERED	6/22/06

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EXAM. INT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TN	A36	6,350,993 B1	02/26/2002	Chu et al.	---	---	
TN	A37	US 2002/0125471 A1	09/12/2002	Fitzgerald et al.	---	---	12/04/2001
TN	A38	US-2002/140031-A1	10/03/2002	Rim 2502/0140031	---	---	03/31/2001
TN	A39	US 2002/0125497 A1	09/12/2002	Fitzgerald	---	---	07/16/2001

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[illegible]

### OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
TN	C20	Maiti et al., "Strained-Si heterostructure field effect transistors," <u>Semicond. Sci. Technol.</u> , Vol. 13 (1998) pp. 1225-1246.
TN	C21	Hackbarth et al., "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," <u>Journal of Crystal Growth</u> , Vol. 201 (1999) pp. 734-738
TN	C22	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Submitted to the Massachusetts Institute of Technology Department of Electrical Engineering and Computer Science on June 30, 1999, pp. 1-154.
TN	C23	O'Neill et al., "SiGe Virtual substrate N-channel heterojunction MOSFETS," <u>Semicond. Sci. Technol.</u> , Vol. 14 (1999) pp. 784-789.
TN	C24	Rim, "Application of Silicon Based Heterostructures to Enhanced Mobility Metal-Oxide-Semiconductor Field-Effect Transistors," Ph.D. Thesis, Stanford University (July 1999) pp. 1-184
TN	C25	Parker et al., "SiGe heterostructure CMOS circuits and applications," <u>Solid State Electronics</u> , Vol. 43, No. 8, (August 1999) pp. 1497-1506.

EXAMINER	J. N. HUNTER	DATE CONSIDERED	6/22/06
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